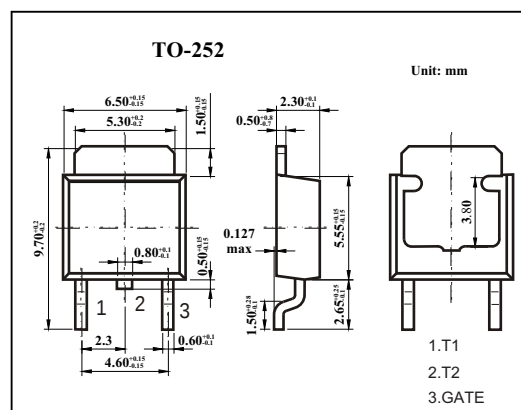
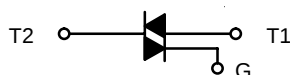


Silicon Bidirectional Thyristors

CR3AM

■ Features

- Blocking voltage to 400 V
- General purpose bidirectional switching

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Repetitive peak off-state voltages	V_{DRM}, V_{RRM}	400	V
RMS on-state current	$I_{T(RMS)}$	3	A
Non-repetitive peak on-state current	I_{TSM}	30	A
Circuit Fusing Considerations ($t = 8.3 \text{ ms}$)	I^2t	3.7	A^2s
Peak Gate Voltage	V_{GM}	6	V
Average Gate Power	$P_{G(AV)}$	0.3	W
Peak Gate Power	P_{GM}	3	W
Peak Gate Current	I_{GM}	0.5	A
Operating Junction Temperature Range	T_J	-40 to 125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-40 to 150	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

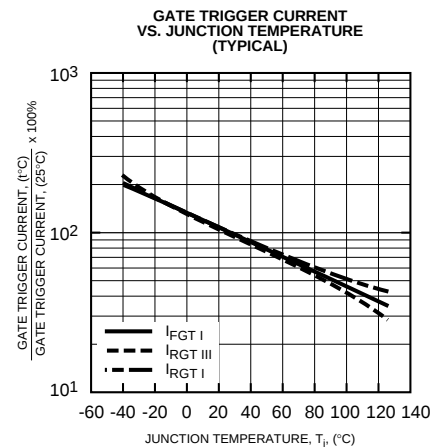
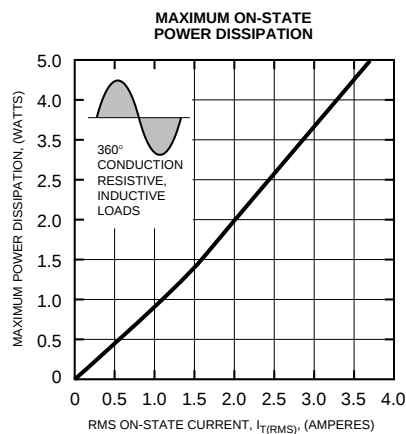
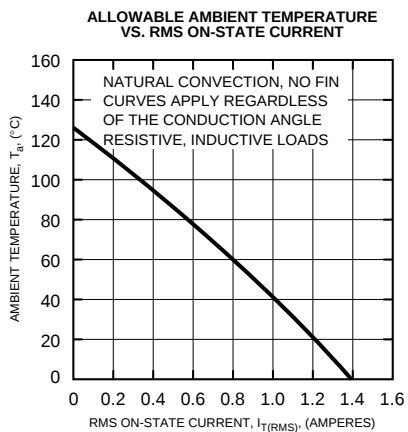
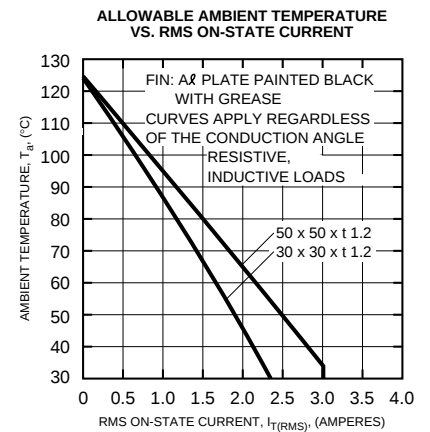
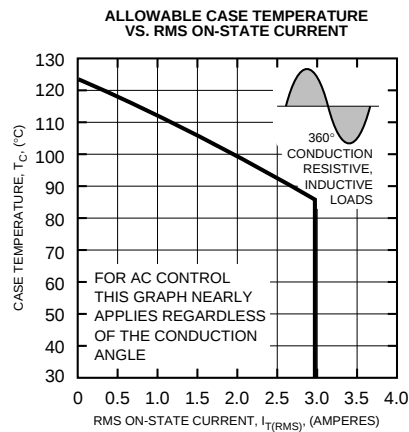
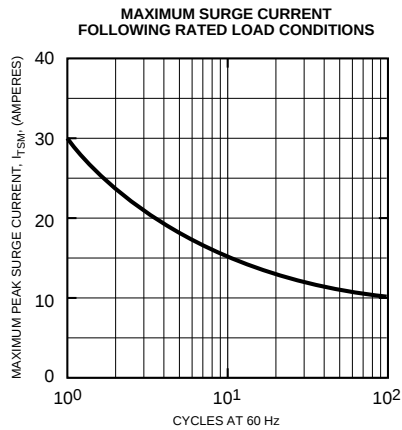
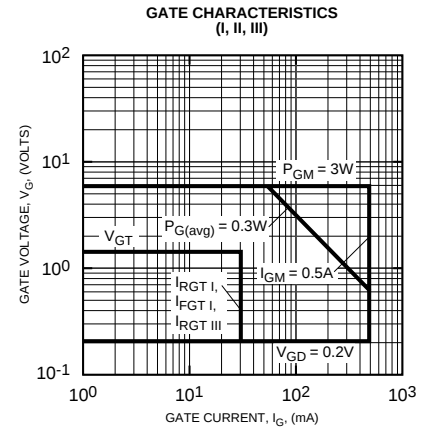
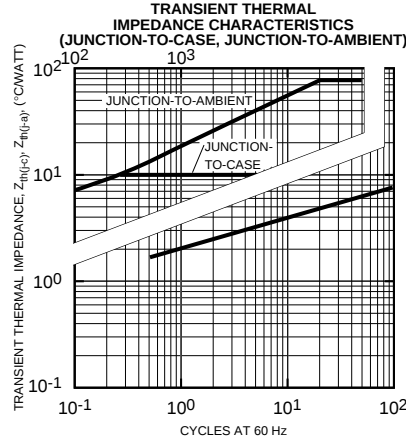
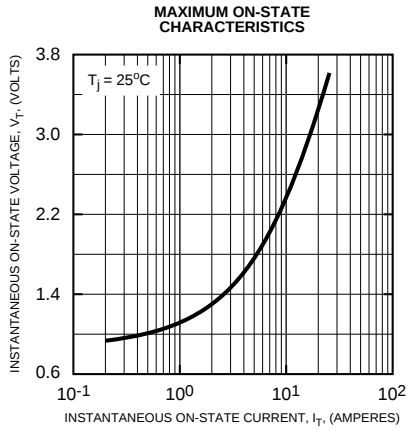
Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Peak Repetitive Blocking Current	I_{DRM}, I_{RRM}	$V_D = \text{Rated } V_{DRM}, V_{RRM}; \text{Gate Open}$			2	mA
Peak On- State Voltage	V_{TM}	$I_T = 4.5 \text{ A}$			1.5	V
Gate trigger current	I_{GT}	$T_2(+), G(+)$			30	mA
		$T_2(+), G(-)$			30	mA
		$T_2(-), G(-)$			30	mA
		$T_2(-), G(+)$			-	mA
Gate trigger voltage	V_{GT}	$T_2(+), G(+)$			1.5	V
		$T_2(+), G(-)$			1.5	V
		$T_2(-), G(-)$			1.5	V
		$T_2(-), G(+)$			-	V
DC Gate Non-trigger Voltage	V_{GD}	$V_D = 1/2 V_{DRM}$	0.2			V

■ Marking

Marking	CR3AM
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CR3AM

■ Typical Characteristics



CR3AM

